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APPLICATION NO. FILING DATE		LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/540,514	10/540,514 06/23/2005		Takenori Osada	Q88664	6643		
23373	7590	10/11/2006		EXAM	EXAMINER		
SUGHRUE		PLLC A AVENUE, N.W.	LIU, BENJAMIN T				
SUITE 800	SILVANI	A AVENUE, N.W.	ART UNIT	PAPER NUMBER			
WASHING	TON, DC	20037	2826				

DATE MAILED: 10/11/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

		Applicat	ion No.	Applicant(s)			
				OSADA ET AL.			
	Office Action Summary	10/540,5 Examine		Art Unit			
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	The MAILING DATE of this communi	Benjamin		2826 correspondence add			
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WHIC - Exter after - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR CHEVER IS LONGER, FROM THE MANSIONS OF THE MANSIO	AILING DATE OF T of 37 CFR 1.136(a). In no e- unication. tutory period will apply and v will, by statute, cause the ap	HIS COMMUNICATION went, however, may a reply be will expire SIX (6) MONTHS from plication to become ABANDO	ON. timely filed om the mailing date of this com NED (35 U.S.C. § 133).			
Status							
1)🖂	Responsive to communication(s) file	d on <u>28 June 2006</u> .					
2a) <u></u> □	This action is FINAL .	b)⊠ This action is	non-final.				
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
	closed in accordance with the practic	e under <i>Ex parte Q</i>	uayle, 1935 C.D. 11,	453 O.G. 213.			
Dispositi	ion of Claims						
4)⊠	Claim(s) <u>1-8</u> is/are pending in the ap	plication.		•			
,	4a) Of the above claim(s) <u>5-8</u> is/are v	•	ideration.	_			
	Claim(s) is/are allowed.		¢.	Bull	Tomas		
	Claim(s) <u>1-4</u> is/are rejected.						
7)	Claim(s) is/are objected to.			Minhloan Tran			
8)⊠	Claim(s) are subject to restriction	and/or election req	uirement.	Primary Examin Art Unit 2826	ier		
Annliaati	ion Panam			Art Onit 2020			
	ion Papers						
•	The specification is objected to by the			a Everniner	•		
10)	The drawing(s) filed on is/are:	·	•				
	Applicant may not request that any object Replacement drawing sheet(s) including				R 1 121(d)		
11)	The oath or declaration is objected to						
·	under 35 U.S.C. § 119	-,					
•	•			(a) (d) an (f)			
	Acknowledgment is made of a claim	for foreign priority ui	nder 35 U.S.C. § 119	(a)-(u) or (i).			
a)	✓ All b) Some * c) None of:1. Certified copies of the priority	documents have he	en received				
	2. Certified copies of the priority			ation No			
	3. Copies of the certified copies				Stage		
	application from the Internatio						
* (See the attached detailed Office action	•	• • •	ived.			
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Attachmen	it(s)						
	ce of References Cited (PTO-892)	·	4) Interview Summa				
	ce of Draftsperson's Patent Drawing Review (Pmation Disclosure Statement(s) (PTO/SB/08)	10-948)	Paper No(s)/Mail 5) Notice of Informa	al Patent Application			
	er No(s)/Mail Date		6) Other:				

DETAILED ACTION

Election/Restrictions

1. Newly submitted claim 5-8 directed to an invention that is independent or distinct from the invention originally claimed for the following reasons:

Restriction to one of the following inventions is required under 35 U.S.C. 121:

- Claims 1-4, drawn to semiconductor device, classified in class 257, subclass 11.
- II. Claims 5-8, drawn to method of manufacturing a semiconductor device, classified in class 438, subclass 172.

The inventions are distinct, each from the other because of the following reasons:

Inventions II and I are related as process of making and product made. The inventions are distinct if either or both of the following can be shown: (1) that the process as claimed can be used to make another and materially different product or (2) that the product as claimed can be made by another and materially different process (MPEP § 806.05(f)). In the instant case the group II process of employing a metalorganic chemical vapor deposition method could be substituted with sputtering.

Because these inventions are independent or distinct for the reasons given above and there would be a serious burden on the examiner if restriction is not required because the inventions have acquired a separate status in the art in view of their different classification, restriction for examination purposes as indicated is proper.

Since applicant has received an action on the merits for the originally presented invention, this invention has been constructively elected by original presentation for

prosecution on the merits. Accordingly, claims 5-8 withdrawn from consideration as being directed to a non-elected invention. See 37 CFR 1.142(b) and MPEP § 821.03.

Claim Rejections - 35 USC § 102(e)

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-3 are rejected under 35 U.S.C 102(e) as being anticipated by Taylor (2003/0006407).

With regard to claim 1, figures 1A and 2I of Taylor disclose a compound semiconductor epitaxial substrate for use in a strain channel high electron mobility field effect transistor, comprising an InGaAs layer 160 as a strain channel layer and an AIGaAs layer 163 containing n-type impurities as an electron supplying layer, wherein the InGaAs layer 160 has an emission peak wavelength of 1.1 microns. (Note lines 27-29 in paragraph [0039] of Taylor)

With regard to claim 2, figures 1A and 2I of Taylor disclose a compound semiconductor epitaxial substrate, wherein GaAs layers (158, 161) are provided as

spacer layers in contact with a top surface 161 and a bottom surface 158 of the InGaAs layer 160, respectively.

With regard to claim 3, figures 1A and 2I of Taylor disclose a compound semiconductor epitaxial substrate, wherein each of the GaAs layers (158, 161) has a thickness of 4 nm or more. (Note lines 37-39 and lines 44-45 in paragraph [0033] of Taylor).

Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 4 is rejected under 35 U.S.C 103(a) as being unpatentable over Taylor in view of Matsugatami et al. (5,449,928).

With regard to claim 4, Taylor discloses all the subject matter claimed except for a compound semiconductor epitaxial substrate, wherein the InGaAs layer has an electron mobility at 300 K of 8300 cm2/V•s or more.

However, figure 2 of Matsugatani et al. discloses a compound semiconductor epitaxial substrate, wherein the InGaAs layer 3 has an electron mobility at 300 K of 11500 cm²/Vs. (Note lines 16-30 in column 6 of Matsugatani et al.)

Therefore, it would have been obvious to one of ordinary skill in the art to form the compound semiconductor of Taylor with the channel of Matsugatani et al. in order to increase the channel mobility.

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Benjamin T. Liu whose telephone number is (571) 272-6009. The examiner can normally be reached on Mon-Fri 9:30 AM-6:00AM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on 571 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BTL 10/2/2006